



iJew
Attorney Docket No. _____
Patent
005950-844

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of
Shenggao Liu et al.

Application No.: 10/764,407

Group Art Unit: 1755

Filing Date: January 23, 2004

Examiner:

Title: PHOTORESIST COMPOSITIONS COMPRISING DIAMONDOID DERIVATIVES

Confirmation No.: 9511

**FIRST
INFORMATION DISCLOSURE STATEMENT
TRANSMITTAL LETTER**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Enclosed is a FIRST Information Disclosure Statement and accompanying form PTO-1449 for the above-identified patent application.

- No additional fee for submission of an IDS is required.
- The fee of \$180.00 (1806) as set forth in 37 C.F.R. § 1.17(p) is also enclosed.
- A statement under 37 C.F.R. § 1.97(e) is also enclosed.
- A statement under 37 C.F.R. § 1.97(e), and the fee of \$180.00 (1806) as set forth in 37 C.F.R. § 1.17(p) are also enclosed.
- Charge _____ to Deposit Account No. 02-4800 for the fee due.
- A check in the amount of _____ is enclosed for the fee due.
- Charge _____ to credit card. Form PTO-2038 is attached.

The Director is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17 and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 02-4800. This paper is submitted in duplicate.

Respectfully submitted,

BURNS, DOANE, SWECKER & MATHIS, L.L.P.

By

Stephen F. Powell

Stephen F. Powell
Registration No. 43,014

Date: 10-14-04

BURNS DOANE
BURNS DOANE SWECKER & MATHIS LLP
INTELLECTUAL PROPERTY LAW

**FIRST
INFORMATION DISCLOSURE STATEMENT
TRANSMITTAL LETTER**

(4/04)



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Shenggao Liu et al.) Group Art Unit: 1755
Application No.: 10/764,407) Examiner:
Filed: January 23, 2004) Confirmation No.: 9511
For: PHOTORESIST COMPOSITIONS)
COMPRISING DIAMONDOID)
DERIVATIVES)
)

FIRST INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. § 1.56, the accompanying information is being submitted in accordance with 37 C.F.R. §§ 1.97 and 1.98.

Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed. However, copies of the listed U.S. patents and U.S. patent application publications are not enclosed since it is no longer required according to the July 11, 2003 waiver of the requirement for copies of cited U.S. patents and U.S. patent application publications in national patent applications filed after June 30, 2003 and international applications entering the national stage under 35 U.S.C. § 371 after June 30, 2003.

The documents are being submitted within three (3) months of the filing or entry of the national stage of this application or before the first Office Action on the merits, whichever is later. Since these documents are being filed within the time period set forth in 37 C.F.R. § 1.97(b), no fee or statement is required.

FIRST Information Disclosure Statement
Application No. 10/764,407
Attorney's Docket No. 005950-844
Page 2

To assist the Examiner, the document is / documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initialed copy of this form be returned to the undersigned.

Respectfully submitted,

BURNS, DOANE, SWECKER & MATHIS, L.L.P.

Date 10-14-04

By: Stephen F. Powell
Stephen F. Powell
Registration No. 43,014
Redwood Shores, California Office
(650) 622-2300

P.O. Box 1404
Alexandria, Virginia 22313-1404

**FIRST
INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

Sheet 1 of 6

3

(List any other effects as necessary)

Complete if Known

Application Number	10/764,407
Filing Date	January 23, 2004
First Named Inventor	Shenggao Liu et al.
Examiner Name	

Attorney Docket Number 005950-844

OCT 15 2004

U.S. PATENT DOCUMENTS

Examiner Initials	Document Number	Kind Code (if known)	Name of Patentee or Applicant of Cited Document	Issue/Publication Date (MM-DD-YYYY)
	5,166,313	528/344	Archibald et al.	11/24/92
	5,399,647	526/297	Nozaki	03/21/95
	5,621,019	522/49	Nakano et al.	04/15/97
	5,665,518	430/270.1	Maeda et al.	09/09/97
	5,691,111	430/270.1	Iwasa et al.	11/25/97
	5,756,850	568/75	Iwasa et al.	05/26/98
	5,929,271	560/126	Hada et al.	07/27/99
	6,042,991	430/285.1	Aoai et al.	03/28/00
	6,071,670	430/270.1	Ushirogouchi et al.	06/06/00
	6,077,644	430/270.1	Hada et al.	06/20/00
	6,087,063	430/270.1	Hada et al.	07/11/00
	6,103,445	430/270.1	Wilson et al.	08/15/00
	6,124,074	430/270.1	Varanasi et al.	09/26/00
	6,136,501	430/270.1	Trefonas, III et al.	10/24/00
	6,200,724	430/270.1	Namiki et al.	03/13/01
	6,200,728	430/270.1	Cameron et al.	03/13/01
	6,225,019	430/270.1	Matsuda et al.	05/01/01
	6,225,476	549/323	Hada et al.	05/01/01
	6,238,842	430/281.1	Sato et al.	05/29/01
	6,245,485	430/288.1	Aoai et al.	06/12/01
	6,251,569	430/325	Angelopoulos et al.	06/26/01
	6,268,106	430/270.1	Park et al.	07/31/01
	6,291,130	430/270.1	Kodama et al.	09/18/01
	6,306,554	430/270.1	Barclay et al.	10/23/01
	6,313,327	552/553	Seo et al.	11/06/01
	6,344,590	568/591	Nakano et al.	02/05/02
	6,380,270	521/50.5	Yates	04/30/02
	6,383,713	430/270.1	Uetani et al.	05/07/02
	6,388,101	549/318	Hada et al.	05/14/02
	6,391,520	430/270.1	Nakano et al.	05/21/02
	6,403,280	430/270.1	Yamahara et al.	06/11/02
	6,403,823	560/116	Hasegawa et al.	06/11/02
	6,416,925	430/270.1	Aoai et al.	07/09/02
	6,440,636	430/270.1	Ushirogouchi et al.	08/27/02
	6,462,158	526,282	Miwa et al.	10/08/02
	6,465,137	430/5	Watanabe et al.	10/15/02
	6,479,211	430/270.1	Sato et al.	11/12/02
	6,486,330	549/270	Nakano	11/26/02
	6,489,082	430/313	Hattori et al.	12/03/02
	6,492,086	430/270.1	Barclay et al.	12/10/02
	6,498,226	528/170	Cheng et al.	12/24/02
	6,517,991	430/270.1	Kodama et al.	02/11/03
	6,548,221	430/270.1	Uetani et al.	04/15/03
	6,552,143	526/271	Funaki et al.	04/22/03
	6,555,289	430/270.1	Sasaki et al.	04/29/03
	6,562,554	430/326	Varanasi et al.	05/13/03
	6,566,038	430/270.1	Nishi et al.	05/20/03

Examiner Signature

Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with M.P.E.P. § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

**FIRST
INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 2 of 3

Complete if Known

Application Number	10/764,407
Filing Date	January 23, 2004
First Named Inventor	Shenggao Liu et al.
Examiner Name	
Attorney Docket Number	005950-844

U.S. PATENT DOCUMENTS

Examiner Initials	Document Number	Kind Code (if known)	Name of Patentee or Applicant of Cited Document	Issue/Publication Date (MM-DD-YYYY)
	2001/0026901	430/270.1	Maeda et al.	10/04/01
	2002/0016516	568/818	Nakano et al.	02/07/02
	2002/0037472	430/270.1	Zampini et al.	03/28/02
	2002/0048720	430/270.1	Sasaki et al.	04/25/02
	2002/0064727	430/270.1	Sato	05/30/02
	2002/0076543	428/315.9	Sikonia	06/20/02
	2002/0099147	525/329.7	Yoshida et al.	07/25/02
	2002/0120090	528/170	Cheng et al.	08/29/02
	2002/0123010	430/325	Angelopoulos et al.	09/05/02
	2002/016516	568/818	Nakano et al.	02/07/02
	2002/0169266	526/281	Funaki et al.	11/14/02
	2002/0177743	585/16	Dahl et al.	11/28/02
	2002/0182360	428/40.5	Koshiyama et al.	12/05/02
	2002/0182534	430/270.1	Varanasi et al.	12/05/02
	2002/0187420	430/270.1	Barclay et al.	12/12/02
	2003/0008241	430/287.1	Sato et al.	01/09/03
	2003/0017415	430/287.1	Kodama et al.	01/23/03
	2003/0017635	438/29	Apen et al.	01/23/03
	2003/0031789	427/248.1	Bedwell et al.	02/13/03
	2003/0031949	430/270.1	Barclay et al.	02/13/03
	2003/0031950	430/270.1	Uenishi et al.	03/06/03
	2003/0044717	430/270.1	Kodama	03/06/03
	2003/0044718	430/270.1	Kodama et al.	03/27/03
	2003/0059710	430/270.1	Inoue	04/03/03
	2003/0064327	430/325	Rottstegge	04/10/03
	2003/0068585	430/324	Rottstegge	04/17/03
	2003/0073027	430/270.1	Namiki et al.	06/20/02
	2002/0076543	428/315.9	Sikonia	04/24/03
	2003/0077540	430/270.1	Kodama et al.	04/24/03
	2003/0077543	430/287.1	Sato	06/05/03
	2003/0102285	216/41	Nozaki et al.	06/05/03
	2003/0105264	528/31	Bedwell et al.	06/12/03
	2003/0108809	430/171	Sato	09/05/02
	2003/0123010	430/325	Angelopoulos et al.	07/17/03
	2003/0134225	430/270.1	Fujimori et al.	08/07/03
	2003/0148206	430/127	Kodama	08/07/03
	2003/0148210	430/270.1	Funaki et al.	08/07/03

Examiner Signature	Date Considered
--------------------	-----------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with M.P.E.P. § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

**FIRST
INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 3 of 3

Sheet 3 of 3 Attorney Docket Number 005950-044

FOREIGN PATENT DOCUMENTS

NON-PATENT LITERATURE DOCUMENTS

Examiner Initials	Include name of the author (IN CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
LIAW, Der-Jang,	"Synthesis and characterization of new polyamides and polyimides prepared from 2,2-bis[4-(4-aminophenoxy)phenyl]adamantane," <i>Macromol. Chem. Phys.</i> 200, No. 6, pp. 1326-1332 (1999)
NOZAKI, Koji et al.,	"High-Performance Resist Materials for ArF Excimer Laser and Electron Beam Lithography," <i>FUJITSU Sci Tech.</i> J., 38, 1, pp. 3-12 (June 2002)
PADMANABAN, Munirathna, et al.,	"Etch Properties of 193nm Resists: Issues and Approaches," <i>Journal of Photopolymer Science and Technology</i> , Vol 15, No. 3 (2002), pp. 521-528
PADMANABAN, Munirathna, et al.,	"Layer-Specific Resists for 193nm Lithography," <i>Journal of Photopolymer Science and Technology</i> , Vol. 13, No. 4 (2000) pp. 607-616
PANIEZ, P. J., et al.,	"Thermal Phenomena in Acrylic 193 nm Resists," SPIE Conferences on Advances in Resist Technology and Processing XVI, Santa Clara, CA, SPIE Vol. 3678 pp. 1352-1363
SHIDA, Naomi,	"Advanced Materials for 193-nm Resists," <i>Journal of Photopolymer Science and Technology</i> , Vol. 13, No. 4 (2000) pp. 601-606
USHIROGOUCHI, Tohru, et al.,	"Advanced Materials for 193-nm Resists," In <i>Advances in Resist Technology and Processing XVII</i> , Francis M. Houlahan, Editor, Proceedings of SPIE Vol. 3999 (2000) pp. 1147-1156

Examiner Signature _____ **Date Considered** _____
Comments with M.R.E.P. § 509. Draw line through citation if not in

***EXAMINER:** Initial if reference considered, whether or not citation is in conformance with M.P.E.P. § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.